## Supporting Information

## **Oxygen-Deficient Dopant-Free Ti3O<sup>5</sup> and Ti2O<sup>3</sup> Ferromagnetic Nanostructures for Spin-Based Electronic Devices**

*Md Anisur Rahman, Joseph Palathinkal Thomas, Mahdi Beedel, Xiaoyi Guan, Nina F. Heinig, Lei Zhang, and Kam Tong Leung\**

*M. A. Rahman, J. P. Thomas, M. Beedel, X. Guan, N. F. Heinig, L. Zhang, and K. T. Leung*

*Department of Chemistry, University of Waterloo, 200 University Ave W, Waterloo, ON, N2L 3G1, Canada*



Figure S1. SEM images of titanium suboxide nanobricks grown on H-Si templates in 0.200 Torr Ar at (a)  $680 °C$  and (b)  $820 °C$ .



Figure S2: Raman spectra of as-deposited titanium suboxide nanostructures obtained at different temperatures and of commercial  $TiO<sub>2</sub>$  rutile powder.



Figure S3: *M–H* curves of the H-Si and Au/H-Si substrates at 750 °C and 780 °C.



Figure S4: Typical XPS survey spectrum for the NW 750 °C nanowall film. Similar survey spectra have also been observed for the other nanostructured films (not shown).



Figure S5: *M–H* curves of (a) the NW 720 °C and (c) NB 820 °C samples measured at 5, 100, 300, and 400 K. The insets show the magnified hysteresis loops near the origin at 5 and 400 K. Magnetization as a function of temperature for (b) the NW 720  $^{\circ}$ C and (d) NB 820  $^{\circ}$ C films following field-cooled and zero-field-cooled measurements at  $H = 100$  Oe.



Figure S6: XPS spectra of the Ti 2p<sub>3/2</sub> and O 1s regions of the corresponding NW 780 °C, NW 750 °C, and commercial  $Ti<sub>3</sub>O<sub>5</sub>$  and  $Ti<sub>2</sub>O<sub>3</sub>$  powders.

Table 2: Comparison of room-temperature saturation ferromagnetism in different dilute magnetic semiconductor systems.



- 1 M. A. Rahman, S. Rout, J. P. Thomas, D. McGillivray and K. T. Leung, *J. Am. Chem. Soc.*, 2016, **138**, 11896–11906.
- 2 B. Santara, P. K. Giri, K. Imakita and M. Fujii, *Nanoscale*, 2013, **5**, 5476–5488.
- 3 H. Wang, J. Wei, R. Xiong and J. Shi, *J. Magn. Magn. Mater.*, 2012, **324**, 2057–2061.
- 4 S. K. S. Patel and N. S. Gajbhiye, *J. Magn. Magn. Mater.*, 2013, **330**, 21–24.
- 5 P. Sharma, A. Gupta, K. V. Rao, F. J. Owens, R. Sharma, R. Ahuja, J. M. O. O. Guillen, B. Johansson and G. A. Gehring, *Nat. Mater.*, 2003, **2**, 673–677.
- 6 S. B. Singh, Y.-F. Wang, Y.-C. Shao, H.-Y. Lai, S.-H. Hsieh, M. V. Limaye, C.-H. Chuang, H.-C. Hsueh, H. Wang, J.-W. Chiou, H.-M. Tsai, C.-W. Pao, C.-H. Chen, H.-J.

Lin, J.-F. Lee, C.-T. Wu, J.-J. Wu, W.-F. Pong, T. Ohigashi, N. Kosugi, J. Wang, J. Zhou, T. Regier and T.-K. Sham, *Nanoscale*, 2014, **6**, 9166.

- 7 J. Chaboy, R. Boada, C. Piquer, M. A. Laguna-Marco, M. García-Hernández, N. Carmona, J. Llopis, M. L. Ruíz-González, J. González-Calbet, J. F. Fernández and M. A. García, *Phys. Rev. B*, 2010, **82**, 064411.
- 8 A. K. Rumaiz, B. Ali, A. Ceylan, M. Boggs, T. Beebe and S. Ismat Shah, *Solid State Commun.*, 2007, **144**, 334–338.
- 9 L. Sangaletti, M. C. Mozzati, P. Galinetto, C. B. Azzoni, A. Speghini, M. Bettinelli and G. Calestani, *J. Phys. Condens. Matter*, 2006, **18**, 7643–7650.
- 10 R. K. Singhal, A. Samariya, S. Kumar, Y. T. Xing, D. C. Jain, S. N. Dolia, U. P. Deshpande, T. Shripathi and E. B. Saitovitch, *J. Appl. Phys.*, 2010, **107**, 113916.
- 11 G. S. Chang, J. Forrest, E. Z. Kurmaev, A. N. Morozovska, M. D. Glinchuk, J. A. McLeod, A. Moewes, T. P. Surkova and N. H. Hong, *Phys. Rev. B*, 2012, **85**, 165319.
- 12 Y. F. Lee, F. Wu, R. Kumar, F. Hunte, J. Schwartz and J. Narayan, *Appl. Phys. Lett.*, 2013, **103**, 112101.
- 13 V. Fernandes, R. J. O. Mossanek, P. Schio, J. J. Klein, A. J. A. de Oliveira, W. A. Ortiz, N. Mattoso, J. Varalda, W. H. Schreiner, M. Abbate and D. H. Mosca, *Phys. Rev. B*, 2009, **80**, 035202.
- 14 S. Mahadeva, J. Fan, A. Biswas, K. Sreelatha, L. Belova and K. Rao, *Nanomaterials*, 2013, **3**, 486–497.